

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (cancelled)
2. (Original) A method for manufacturing a single crystal semiconductor, in which a seed crystal is dipped into melt in a crucible and is pulled up to manufacture the single crystal semiconductor having an impurity added thereto, wherein,
in a process of pulling up the single crystal semiconductor, a pulling-up speed fluctuation width in 10 seconds is adjusted to less than 0.025 mm/min.
3. (cancelled)
4. (original) The method for manufacturing the single crystal semiconductor of claim 2, wherein, when the pulling-up speed is controlled such that a diameter of the single crystal semiconductor is adjusted to a desired diameter, a magnetic field of 1500 gauss or above is applied to the melt.
5. (amended) The method for manufacturing the single crystal semiconductor of claim 24, wherein the impurity to be added into the single crystal semiconductor is boron B or gallium Ga, and the impurity concentration is 8.0×10^{17} atoms/cc or more.
6. (amended) The method for manufacturing the single crystal semiconductor of claim 24, wherein the impurity to be added into the single crystal semiconductor is phosphorus P, antimony Sb, or arsenic As, and the impurity concentration is 5.0×10^{17} atoms/cc or more.